



Automotive Power Solutions

March, 2009
Alain Laprade

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Note:

- A standard part without any flow code does not guarantee automotive grade.
- To ensure automotive grade, an _F085 flow code suffix needs to be added to the base part.
- Please contact your local Fairchild sales representative if you experience any problems when ordering.

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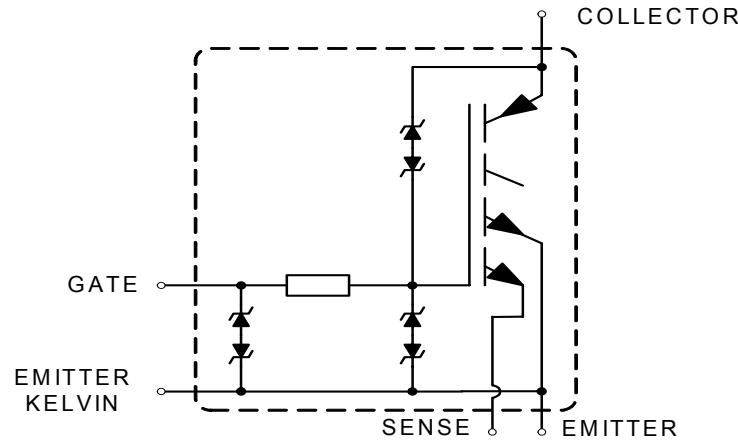


IGBTs

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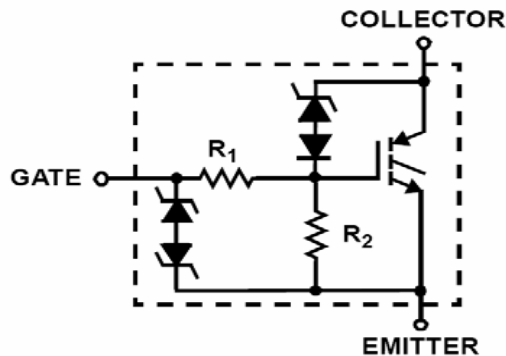
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Current Sensing Ignition IGBTs (AEC-Q101 Qualified)



Type	Clamping IC @110°C Voltage	Design Ratio	$V_{CE(sat)}$ @25°C Max Conditions	SCIS Energy	Package
<u>FGB3040CS</u>	400V	19A	1.6V 6A, 4V	300mJ	TO263-6

Ignition IGBTs (AEC-Q101 Qualified)



Type	Clamping Voltage	I_C @110°C	$V_{CE(sat)}$ Max	@25°C Conditions	SCIS Energy	Package
<u>ISL9V2040S3ST/D3ST</u>	400V	10A	1.45V	6A, 4V, 25°C	200mJ	TO263/TO252
<u>ISL9V2540S3ST</u>	400V	10A	1.45V	6A, 4V, 25°C	250mJ	TO263
<u>ISL9V3036S3ST/D3ST</u>	360V	17A	1.25V	6A, 4V, 25°C	300mJ	TO263/TO252
<u>FGI3236 F085</u>	360V	26A	1.4V	6A, 4V, 25oC	320mJ	TO262
<u>ISL9V3040P3/S3ST/D3ST</u>	400V	17A	1.25V	6A, 4V, 25°C	300mJ	TO220/TO263/TO252
<u>ISL9V5036S3ST/S3</u>	360V	31A	1.17V	10A, 4V, 25°C	500mJ	TO263/TO262
<u>ISL9V5036P3 F085</u>	360V	31A	1.17V	10A, 4V, 25°C	500mJ	TO220
<u>ISL9V5045S3ST</u>	480V	43A	1.25V	10A, 4V, 25°C	500mJ	TO263

IGBTs

(AEC-Q101 Qualified)



Type	V_{CES}	$I_C @ 25^\circ C$	$V_{CE(sat)}$ Max @ 25°C	Package
<u>FGD3N60LSDTM</u>	600V	6A	1.5V @ 3A	TO252

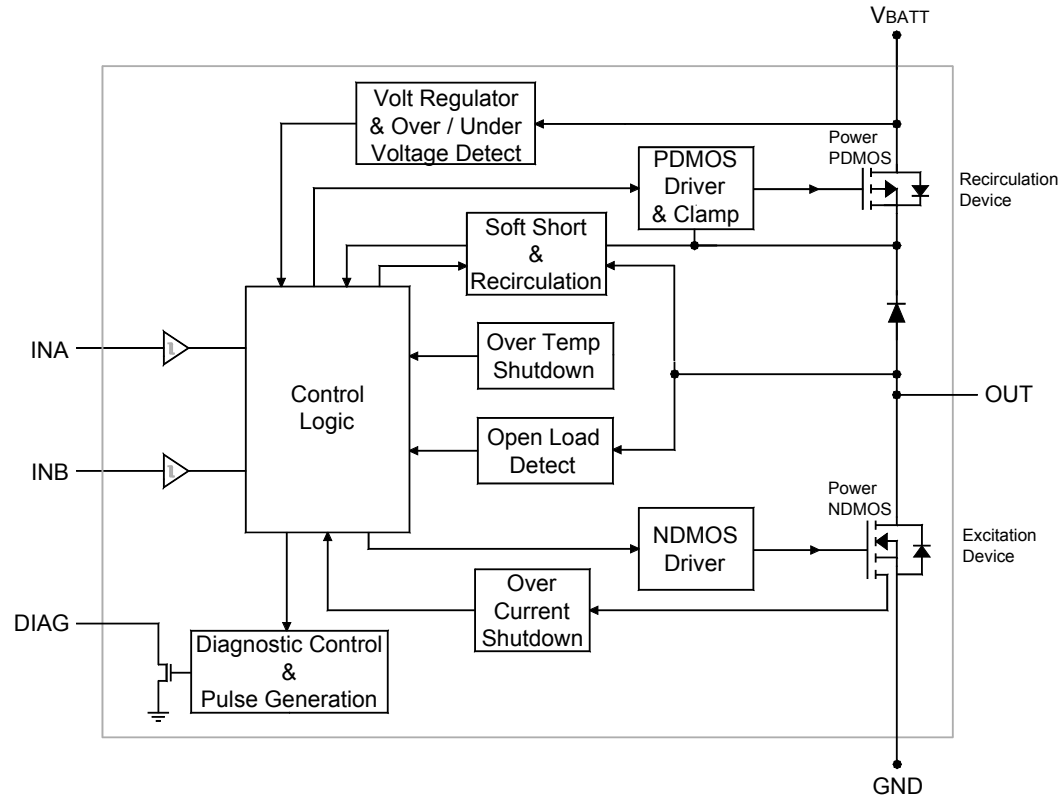


Application Specific Devices

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Dual Integrated Solenoid Driver (AEC-Q100 Qualified)



DUAL INTEGRATED SOLENOID DRIVER

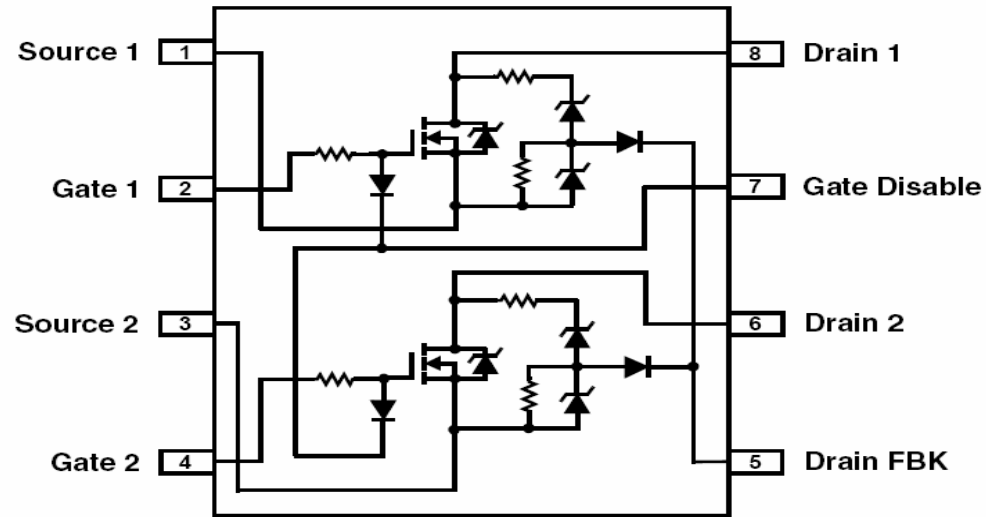
Type	Operation	Function	Package
FDMS2380	6-26V	Transition Solenoid Driver	PQFN

Integrated Injector Driver

NMOS with Gate Disable and Flyback Detection (AEC-Q101 Qualified)

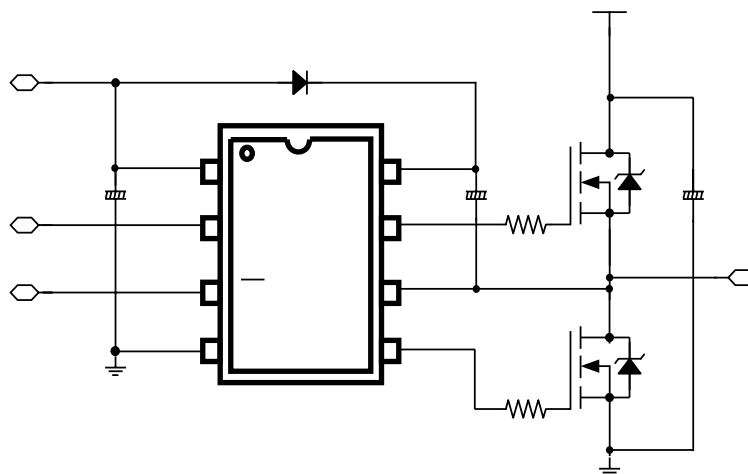


Internal Diagram



Type	BVDss	Gate Drive	$R_{DS(ON)}$	Package
<u>FDSS2407</u>	62V	LL	2x132mOhms	SO8 dual

$R_{DS(ON)}$ listed is rated max at 10V gate drive for standard gate (SG) and 5V gate drive for logic level (LL) devices.



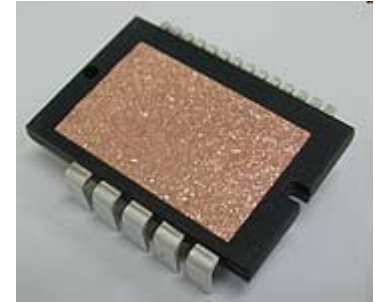
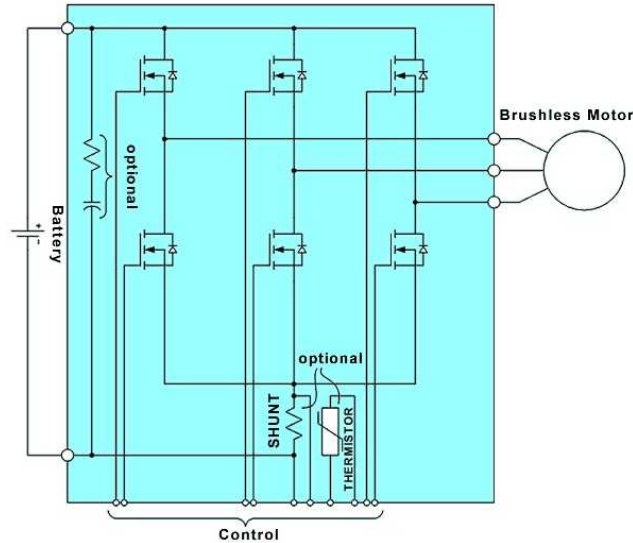
GATE DRIVE ICs Type	Function	Package
<u>FAN7080 F085</u>	Half bridge driver with dead time control	SO8
<u>FAN7081 F085</u>	High side driver	SO8
<u>FAN7083 F085</u>	High side driver with shutdown function	SO8
<u>FAN7085 F085</u>	High side driver with built in recharge	SO8



Power Modules

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Type	BVDss	RMS [1]	I _{phase} typical [2]	R _{θJS} R _{DS(ON)} [3]	MOSFET resistance [4]	Max loop
<u>FTCO353V45A1</u>		40V	170A	1.2°C/W	0.85mΩ	4.6mΩ
<u>FTCO353V455A1</u>		40V	130A	1.3°C/W	1.2mΩ	5.5mΩ
<u>FTCO353V46A1</u>		40V	95A	1.6°C/W	1.5mΩ	6.7Ω

[1] T_{J,max} = 150°C, T_{sink} = 80°C, switching losses = 50% overall losses

[2] Assumes thermal interface material bondline < 40μm and thermal conductivity 1.8 W/m*K

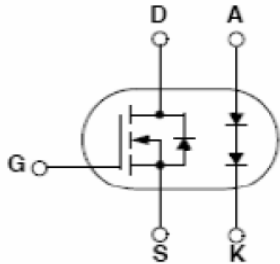
[3] T_J = 25°C

[4] Batt(+) to GND with two phases shorted (includes R_{DS(ON)} of 2 MOSFETs); T_{case} = 25°C

N-Channel Trench MOSFETs

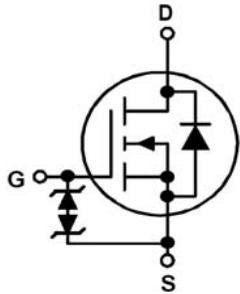
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Temperature Sensing

Type	BVDss	Gate Drive	$R_{DS(ON)}$	Package
FDB8444TS	40V	SG	5.0mOhms	TO263-5



ESD Protected

Type	BVDss	Gate Drive	$R_{DS(ON)}$	Package
FDD8453LZ F085 [1]	40V	LL	8.7mOhms	TO252

[1] $R_{DS(ON)}$ specified for 4.5V gate drive.

$R_{DS(ON)}$ listed is rated max at 10V gate drive for standard gate (SG) and 5V gate drive for logic level (LL) devices.

N-Channel Trench MOSFETs (AEC-Q101 Qualified)



Type	BVDss	Gate Drive	R _{DS(ON)}	Package
<u>FDG6301N F085</u>	25V	LLL	2x5 Ohms	SC70-6 dual
<u>FDB8832 F085</u>	30V	LL	2.1mOhms	TO263
<u>FDB8860 F085</u>	30V	LL	2.6mOhms	TO263
<u>FDD8870 F085</u> [1]	30V	LL	4.4mOhms	TO252
<u>FDB/P8870 F085</u> [1]	30V	LL	4.4mOhms	TO263/TO220
<u>FDB/P8896 F085</u> [1]	30V	LL	6.5mOhms	TO263/TO220
<u>FDD8896 F085</u> [1]	30V	LL	6.8mOhms	TO252
<u>FDD8444L F085</u>	40V	LL	6.0mOhms	TO252
<u>FDD8447L F085</u> [1]	40V	LL	11mOhms	TO252
<u>FDB8441 F085</u>	40V	SG	2.5mOhms	TO263
<u>FDP8441 F085</u>	40V	SG	2.7mOhms	TO220
<u>FDI8441 F085</u>	40V	SG	2.7mOhms	TO262
<u>FDB8442 F085</u>	40V	SG	2.9mOhms	TO263
<u>FDI8442 F085</u>	40V	SG	2.9mOhms	TO262
<u>FDP8442 F085</u>	40V	SG	3.1mOhms	TO220
<u>FDB8443 F085</u>	40V	SG	3.0mOhms	TO263
<u>FDP8443 F085</u>	40V	SG	3.5mOhms	TO220
<u>FDD8444 F085</u>	40V	SG	5.2mOhms	TO252
<u>FDB8444 F085</u>	40V	SG	5.5mOhms	TO263
<u>FDD8445 F085</u>	40V	SG	8.7mOhms	TO252
<u>FDB8445 F085</u>	40V	SG	9.0mOhms	TO263

[1] R_{DS(ON)} specified for 4.5V gate drive.

R_{DS(ON)} listed is rated max at 10V gate drive for standard gate (SG) and 5V gate drive for logic level (LL) devices , 2.7V gate drive for low logic level (LLL) devices.

N-Channel Trench MOSFETs (AEC-Q101 Qualified)



Type	BVDss	Gate Drive	R _{DS(ON)}	Package
<u>FDB035AN06A0</u>	60V	SG	3.5mOhms	TO263
<u>FDB050AN06A0</u>	60V	SG	5mOhms	TO263
<u>FDP/FDB070AN06A0</u>	60V	SG	7mOhms	TO220/TO263
<u>FDD10AN06A0</u>	60V	SG	10.5mOhms	TO252
<u>FDP/FDB13AN06A0</u>	60V	SG	13.5mOhms	TO220/TO263
<u>FDD13AN06A0 F085</u>	60V	SG	13.5mOhms	TO252
<u>FDP/FDB20AN06A0</u>	60V	SG	20mOhms	TO220/TO263
<u>FDD20AN06A0 F085</u>	60V	SG	20mOhms	TO252
<u>FDD26AN06A0 F085</u>	60V	SG	26mOhms	TO252
<u>FDB5800</u>	60V	LL	7mOhms	TO263
<u>FDP/FDD14AN06LA0</u>	60V	LL	14.6mOhms	TO220/TO252
<u>FDP24AN06LA0</u>	60V	LL	24mOhms	TO220
<u>FDD24AN06LA0 F085</u>	60V	LL	24mOhms	TO252
<u>FDD5810 F085</u>	60V	LL	27mOhms	TO252
<u>FDC5661N F085</u>	60V	LL	60mOhms	SSOT6
<u>FDN5632N F085</u> [1]	60V	LL	98mOhms	SSOT3
<u>FDB045AN08A0 F085</u>	75V	SG	4.5mOhms	TO263
<u>FDP/FDH047AN08A0</u>	75V	SG	4.7mOhms	TO220/TO247
<u>FDB060AN08A0</u>	75V	SG	6mOhms	TO263
<u>FDP/FDB16AN08A0</u>	75V	SG	16mOhms	TO220/TO263
<u>FDD16AN08A0 F085</u>	75V	SG	16mOhms	TO252

[1] R_{DS(ON)} specified for 4.5V gate drive.

R_{DS(ON)} listed is rated max at 10V gate drive for standard gate (SG) and 5V gate drive for logic level (LL) devices.

N-Channel Trench MOSFETs (AEC-Q101 Qualified)



Type	BVDss	Gate Drive	R _{DS(ON)}	Package
<u>FDP/FDB/FDI/FDH3632</u>	100V	SG	9mOhms	TO220/TO263/TO262/ TO247
<u>FDP3652</u>	100V	SG	16mOhms	TO220
<u>FDB3652 F085</u>	100V	SG	16mOhms	TO263
<u>FDD3672</u>	100V	SG	28mOhms	TO252
<u>FDB3672 F085</u>	100V	SG	28mOhms	TO263
<u>FDP3672</u>	105V	SG	33mOhms	TO220
<u>FDP/FDB/FDD3682</u>	100V	SG	36mOhms	TO220/TO263/TO252
<u>FDP/FDB/FDI2532</u>	150V	SG	16mOhms	TO220/TO263/TO262
<u>FDP/FDB2552</u>	150V	SG	36mOhms	TO220/TO263
<u>FDP/FDB42AN15A0</u>	150V	SG	42mOhms	TO220/TO263
<u>FDS2572</u>	150V	SG	47mOhms	SO8
<u>FDP/FDB2572</u>	150V	SG	52mOhms	TO220/TO263
<u>FDD2572 F085</u>	150V	SG	54mOhms	TO252
<u>FDU2572</u>	150V	SG	54mOhms	TO251
<u>FDD/FDS2582</u>	150V	SG	66mOhms	TO252/SO8
<u>FDD120AN15A0</u>	150V	SG	120mOhms	TO252
<u>FDP2710 F085</u>	250V	HSG	43mOhms	TO220

R_{DS(ON)} listed is rated max at 10V gate drive for standard gate (SG), high standard gate (HSG), and 5V gate drive for logic level (LL) devices.



N-Channel Planar MOSFETs

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N-Channel Planar MOSFETs (AEC-Q101 Qualified)



Type	BVDss	Gate Drive	R _{DS(ON)}	Package
<u>FDH5500 F085</u>	55V	SG	7mOhms	TO247
<u>HUFA75345P3</u>	55V	SG	7mOhms	TO220
<u>HUF75344P3 F085</u>	55V	SG	8mOhms	TO220
<u>HUFA75344S3</u>	55V	SG	8mOhms	TO262
<u>HUFA75321D3S</u>	55V	SG	36mOhms	TO252
<u>HUFA75307T3ST</u>	55V	SG	90mOhms	SOT223

R_{DS(ON)} listed is rated max at 10V gate drive for standard gate (SG) and 5V gate drive for logic level (LL) devices.

N-Channel Planar MOSFETs

(AEC-Q101 Qualified)



Type	BVDss	Gate Drive	R _{DS(ON)}	Package
<u>HUFA76429D3ST F085</u>	60V	LL	25mOhms	TO263
<u>HUFA76429D3</u>	60V	LL	27mOhms	TO251
<u>HUFA76419D3S</u>	60V	LL	43mOhms	TO252
<u>HUFA76413DK8T</u>	60V	LL	2x56mOhms	SO8 dual
<u>HUFA76409D3ST</u>	60V	LL	71mOhms	TO252
<u>HUFA76407D3S</u>	60V	LL	107mOhms	TO252
<u>HUFA76407DK8T</u>	60V	LL	2x105mOhm	SO8 dual
<u>FQT13N06L F085</u>	60V	LL	140mOhms	SOT223
<u>HUFA75645P3</u>	100V	SG	14mOhms	TO220
<u>HUFA75639S3S</u>	100V	SG	25mOhms	TO263
<u>HUFA76645S3ST F085</u>	100V	LL	15mOhms	TO263
<u>HUFA76609D3S F085</u>	100V	LL	165mOhms	TO252

R_{DS(ON)} listed is rated max at 10V gate drive for standard gate (SG) and 5V gate drive for logic level (LL) devices.

N-Channel Planar MOSFETs

(AEC-Q101 Qualified)



Type	BVD _{SS}	Gate Drive	R _{DS(ON)}	Package
<u>HUFA75842P3</u>	150V	SG	42mOhms	TO220
<u>HUFA75852G3</u>	150V	SG	16mOhms	TO247
<u>FQB34N20LTM</u>	200V	LL	80mOhms	TO263
<u>FQD12N20L F085</u>	200V	LL	320mOhms	TO252
<u>FQD10N20L</u>	200V	LL	380mOhms	TO252
<u>FQB/D5N20L</u>	200V	LL	1.25 Ohms	TO263/TO252
<u>FQB/D10N20C</u>	200V	SG	360mOhms	T0263/TO252
<u>FQB34N20</u>	200V	HSG	75mOhms	TO263
<u>FQD18N20V2</u>	200V	HSG	140mOhms	TO252
<u>FQD12N20</u>	200V	HSG	280mOhms	TO252
<u>FQB4N20</u>	200V	HSG	1.4 Ohms	TO263

R_{DS(ON)} listed is rated max at 10V gate drive for standard gate (SG), high standard gate (HSG), and 5V gate drive for logic level (LL) devices.

N-Channel Planar MOSFETs (AEC-Q101 Qualified)



Type	BVD _{SS}	Gate Drive	R _{DS(ON)}	Package
<u>FQD9N25</u>	250V	HSG	470mOhms	TO252
<u>FQB14N30</u>	300V	SG	290mOhms	TO263
<u>FQB25N33</u>	330V	HSG	230mOhms	TO263
<u>FDD6N50TM F085</u>	500V	HSG	900mOhms	TO252
<u>FQD5N60C</u>	600V	SG	2.5Ohms	TO252
<u>FQD2N60C</u>	600V	SG	4.7Ohms	TO252
<u>FQD1N60C</u>	600V	SG	11.5Ohms	TO252
<u>FQD3N60</u>	600V	HSG	3.6Ohms	TO252
<u>FQD1N60</u>	600V	HSG	11.5Ohms	TO252

R_{DS(ON)} listed is rated max at 10V gate drive for standard gate (SG), high standard gate (HSG), and 5V gate drive for logic level (LL) devices.

P-Channel Trench MOSFETs

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P-Channel Trench MOSFETs (AEC-Q101 Qualified)



Type	BVD _{SS}	Gate Drive	R _{DS(ON)}	Package
FDC642P_F085	-20V	LLL	100mOhms	SSOT6
<u>FDD6685</u>	-30V	LL	30mOhms	TO252
<u>FDD6637 F085</u> [1]	-35V	LL	18mOhms	TO252
<u>FDD4141 F085</u> [1]	-40V	LL	18mOhms	TO252
<u>FDD4685 F085</u>	-40V	LL	35mOhms	TO252
<u>FDD4243 F085</u> [1]	-40V	LL	64mOhms	TO252

R_{DS(ON)} listed is rated max at -10V gate drive for standard gate (SG), -5V gate drive for logic level (LL) devices, -1.8V gate drive for low logic level (LLL) devices.

P-Channel Planar MOSFETs

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P-Channel Planar MOSFETs (AEC-Q101 Qualified)



Type	BVD _{SS}	Gate Drive	R _{DS(ON)}	Package
<u>FQP27P06</u>	-60V	SG	70mOhms	TO220
<u>FQB22P10</u> _F085	-100V	SG	125mOhms	TO263
<u>SFW9640</u>	-200V	SG	500mOhms	TO263
<u>FQB5P20</u>	-200V	HSG	1.4 Ohms	TO263
<u>FQD3P50</u> TM_F085	-500V	HSG	4.9 Ohms	TO252
<u>FQD1P50</u>	-500V	HSG	10.5 Ohms	TO252

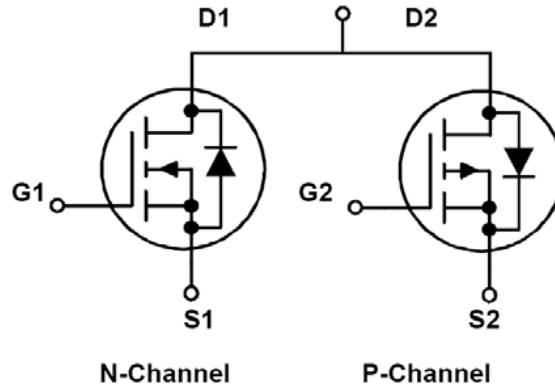
R_{DS(ON)} listed is rated max at -10V gate drive for standard gate (SG) and high standard gate (HSG), -5V gate drive for logic level (LL) devices.

Complimentary Pair Trench MOSFETs

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Complimentary Pair Trench MOSFETs (AEC-Q101 Qualified)



Type	BVD _{SS}	Gate Drive	R _{DS(ON)}	Package
<u>FDD8424H_F085</u> [1]	40V -40V	LL LL	30mOhms 70mOhms	TO252-5

[1] R_{DS(ON)} specified for 4.5V gate drive.

R_{DS(ON)} listed is rated max at 10V gate drive for standard gate (SG) and 5V gate drive for logic level (LL) devices.



Rectifiers

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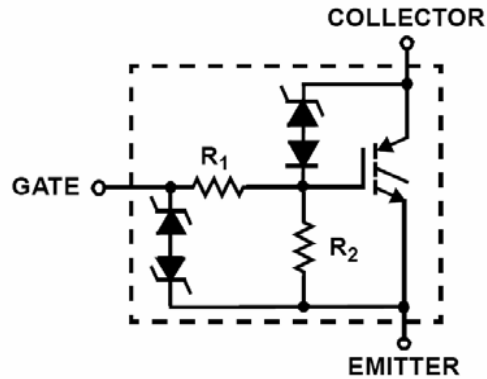
Type	BVD _{ss}	I _F	V _F @ I _F 25°C	Package
Ultrafast Rectifiers				
<u>RURD620CCS9A F085</u>	200V	6A	1.0V	TO252
<u>FFB20UP20DN</u>	200V	2x10A	1.15V	TO263
<u>RUR1S1560S9A</u>	600V	15A	1.5V	TO263
<u>RURD4120S9A</u> F085	1200V	4A	2.1V	TO252
Hyperfast Rectifiers				
<u>RHRD660S9A</u>	600V	6A	2.1V	TO252
<u>RHRP860</u>	600V	8A	2.1V	TO220
Stealth Rectifiers				
<u>ISL9R3060P2</u>	600V	30A	2.4V	TO220

Planned IGBT Devices

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Planned Ignition IGBTs (Will Be AEC-Q101 Qualified)



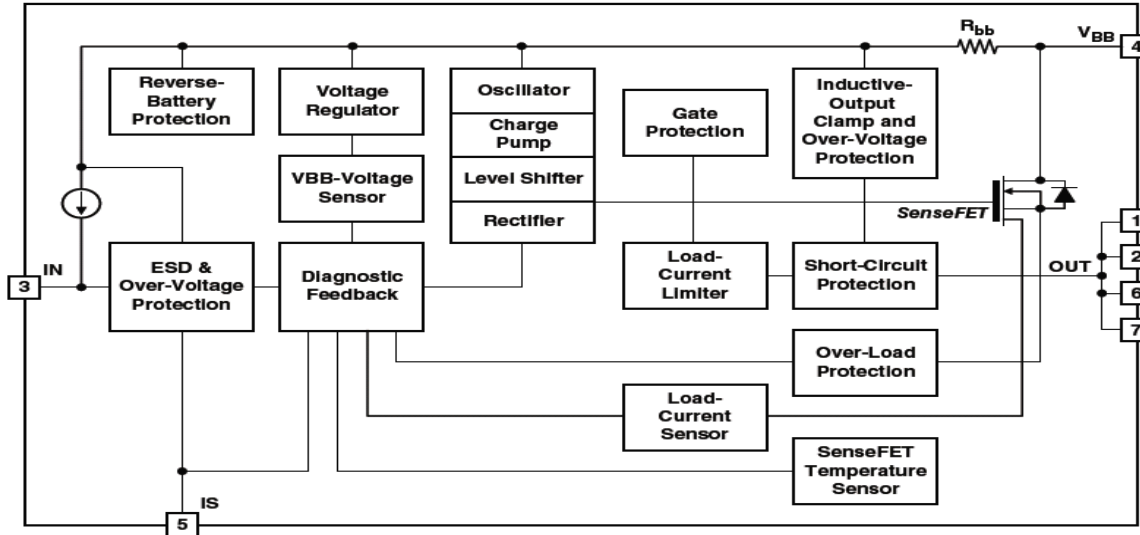
Type	Clamping Voltage	I_C @110°C	$V_{CE(sat)}$ Max @25°C Conditions	SCIS Energy	Package	Samples	Release
FGB3236_F085	360V	26A	1.4V 6A, 4V, 25°C	320mJ	TO263	NOW!	Q2'09

Planned Application Specific Devices

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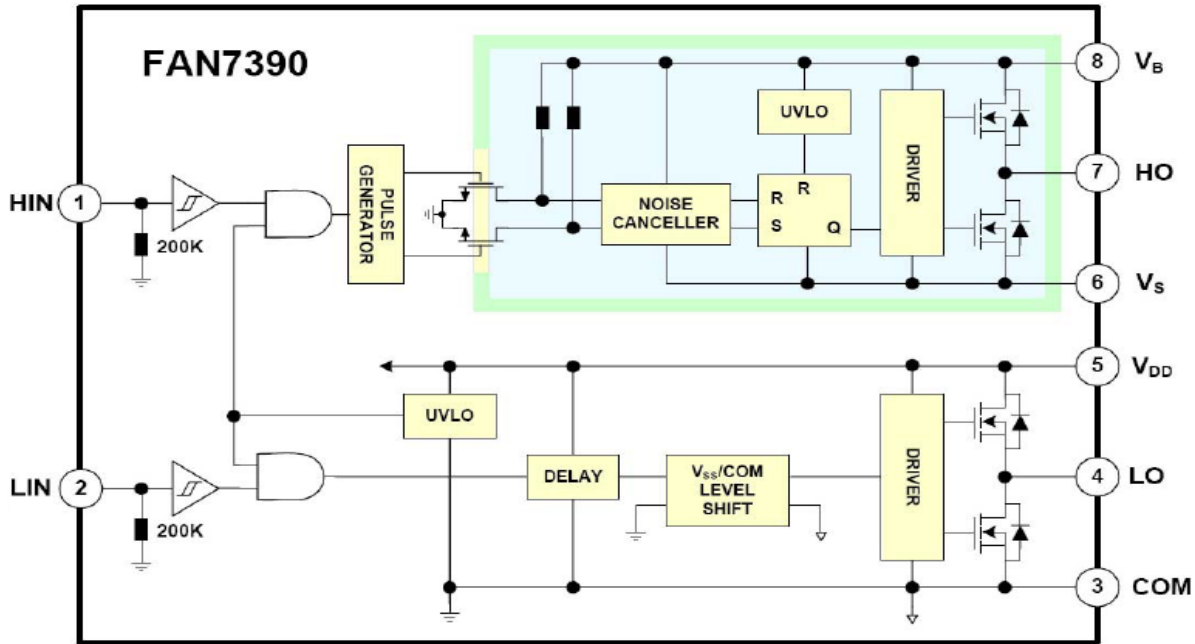
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Planned Application Specific Devices (Will Be AEC-Q101 Qualified)



SMART HIGH SIDE SWITCH MOSFETs

Type	BVDss	$R_{DS(ON)}$	Package	Samples	Release
FDBS09H04	40V	9mOhms	TO263-7	NOW!	Q3'09
FDPS09H04	40V	9mOhms	TO220-7	NOW!	Q3'09
FDSS10H04	40V	10mOhms	TO252-5	NOW!	Q2'09
FDSS100H06	60V	100mOhms	TO252-5	NOW!	Q3'09



GATE DRIVE ICs

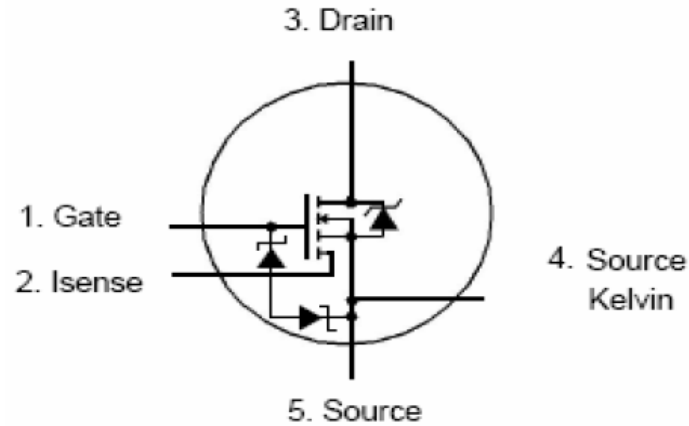
Type	Function	Package	Samples	Release
FAN7190_F085	600V High Current, High and Low Side Gate Drive IC	SO8	Q3'09	Q4'09

Planned N-Channel Trench MOSFETs

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Planned N-Channel Current Sense Trench MOSFETs (Will Be AEC-Q101 Qualified)



Type	BVDss	Gate Drive	$R_{DS(ON)}$	Package	Samples	Release
FDP8444CSZ_F085	40V	SG	5.0mOhms	TO220-5	Q3'09	Q4'09

Planned N-Channel Trench MOSFETs

(Will Be AEC-Q101 Qualified)



Type	BVD _{SS}	Gate Drive	R _{DS(ON)}	Package	Samples	Release
FDB8760_F085	30V	SG	1.6mOhms	TO263	Q3'09	Q3'09
FDD8444R	40V	SG	4.9mOhms	TO252	Q2'09	Q3'09
FDP8445_F085	40V	SG	9.2mOhms	TO220	NOW!	Q2'09
FDS8949_F085 [1]	40V	LL	2x36mOhms	S08 dual	TBD	Q2'09
FDB3601	100V	LL	24mOhms	TO263	TBD	TBD
FDD3601	100V	LL	24mOhms	TO252	TBD	TBD
FDB3602	100V	LL	36mOhms	TO263	TBD	TBD
FDB3605	100V	LL	15mOhms	TO263	TBD	TBD
FDB3901	100V	SG	12mOhms	TO263	TBD	TBD

[1] R_{DS(ON)} specified for 4.5V gate drive.

R_{DS(ON)} listed is rated max at 10V gate drive for standard gate (SG) and high standard gate (HSG), 5V gate drive for logic level (LL) devices.

Planned N-Channel Planar MOSFETs

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Planned N-Channel Planar MOSFETs

(Will Be AEC-Q101 Qualified)



Type	BVD _{SS}	Gate Drive	R _{DS(ON)}	Package	Samples	Release
FDP5500_F085	55V	SG	7mOhms	TO220	NOW!	Q2'09
<u>FQI27N25</u> _F085	250V	HSG	110mOhms	TO262	Q2'09	Q2'09

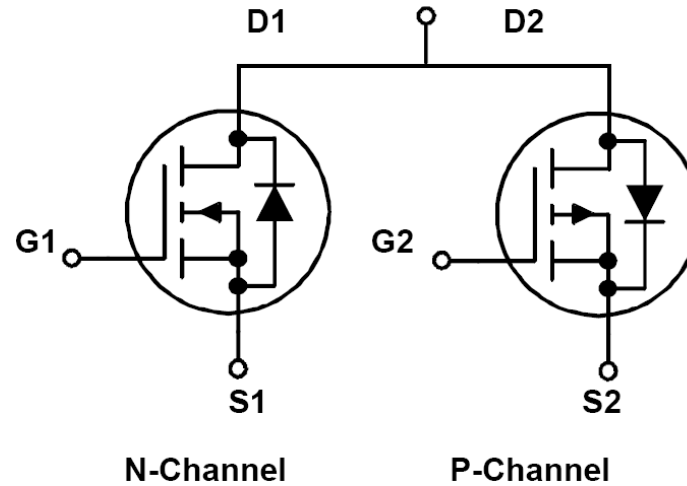
R_{DS(ON)} listed is rated max at 10V gate drive for standard gate (SG) , 5V gate drive for logic level (LL) devices, 1.8V gate drive for low logic level (LLL) devices.

Planned Complimentary Pair Trench MOSFETs

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Planned Complimentary Pair Trench MOSFETs (Will Be AEC-Q101 Qualified)



Type	BVD _{SS}	Gate Drive	R _{DS(ON)}	Package	Samples	Release
FDS4559 F085 [1]	60V -60V	LL LL	75mOhms 135mOhms	SO8 dual	TBD	Q2'09

[1] R_{dson} specified for 4.5V gate drive.

Planned P-Channel Trench MOSFETs

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Planned P-Channel Trench MOSFETs

(Will Be AEC-Q101 Qualified)



Type	BVD _{SS}	Gate Drive	R _{DS(ON)}	Package	Samples	Release
FDS9958 F085 [1]	-60V	LL	135mOhms	SO8	TBD	Q2'09

[1] R_{DS(ON)} specified for 4.5V gate drive.



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Planned P-Channel Planar MOSFETs

(Will Be AEC-Q101 Qualified)



Type	BVD _{SS}	Gate Drive	R _{DS(ON)}	Package	Samples	Release
FQB34P10_F085	-100V	SG	60mOhms	TO263	NOW!	Q2'09

[1] R_{DS(ON)} specified for 4.5V gate drive.



Planned Rectifiers

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Planned Rectifiers

(Will Be AEC-Q101 Qualified)



Type	BVDss	I _F	V _F @ I _F 25°C	Package	Samples	Release
Stealth Rectifiers						
FFD08S60S_F085	600V	8A	2.6V	TO252	NOW!	Q2'09
<u>RUR1S1560S9A</u> _F085	600V	15A	1.5V	TO263	NOW!	TBD